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## 2SC5200/FJL4315 **NPN Epitaxial Silicon Transistor**

### **Applications**

- High-Fidelity Audio Output Amplifier
- General Purpose Power Amplifier

#### Features

- High Current Capability:  $I_C = 17A$ .
- High Power Dissipation : 150watts.
- High Frequency : 30MHz.
- High Voltage : V<sub>CEO</sub>=250V •
- Wide S.O.A for reliable operation.
- Excellent Gain Linearity for low THD.
- Complement to 2SA1943/FJL4215.
- Thermal and electrical Spice models are available.
- · Same transistor is also available in:
  - -- TO3P package, 2SC5242/FJA4313 : 130 watts
  - -- TO220 package, FJP5200 : 80 watts
  - -- TO220F package, FJPF5200 : 50 watts

#### Absolute Maximum Ratings\* T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
BV <sub>CBO</sub>	Collector-Base Voltage	250	V	
BV <sub>CEO</sub>	Collector-Emitter Voltage	250	V	
BV <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current(DC)	17	А	
I <sub>B</sub>	Base Current	1.5	А	
P <sub>D</sub>	Total Device Dissipation(T <sub>C</sub> =25°C) Derate above 25°C	150 1.04	W W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature	- 50 ~ +150	°C	

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### Thermal Characteristics\* T<sub>a=25°C</sub> unless otherwise noted

Symbol	Parameter	Max.	Units	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	0.83	°C/W	

\* Device mounted on minimum pad size

#### h<sub>FE</sub> Classification

Classification	R	0	
h <sub>FE1</sub>	55 ~ 110	80 ~ 160	

1



1.Base 2.Collector 3.Emitter

TO-264

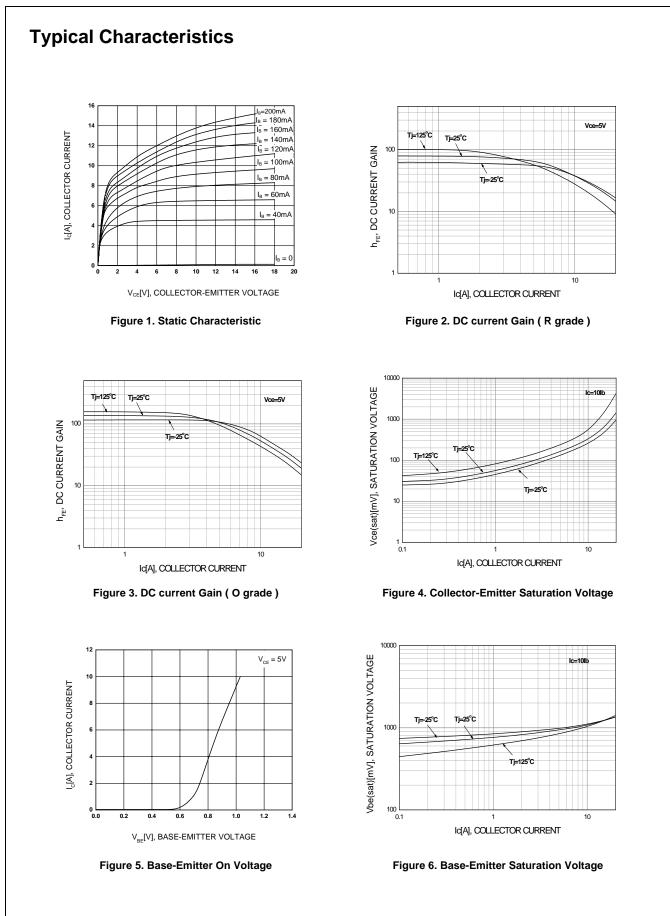
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Electrical Characteristics* T <sub>a</sub> =25°C unless otherwise noted						
Symbol	Parameter	Parameter Test Condition		Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =5mA, I <sub>E</sub> =0	250			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, R <sub>BE</sub> =∞	250			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =5mA, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =230V, I <sub>E</sub> =0			5.0	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =5V, I <sub>C</sub> =0			5.0	μΑ
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	55		160	
h <sub>FE2</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =7A	35	60		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =8A, I <sub>B</sub> =0.8A		0.4	3.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =7A		1.0	1.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =1A		30		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, f=1MHz		200		pF

\* Pulse Test: Pulse Width=20µs, Duty Cycle≤2%

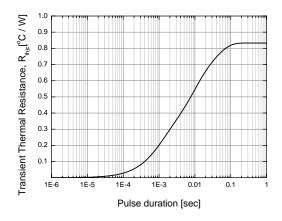
## **Ordering Information**

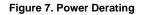
Part Number	Marking	Package	Packing Method	Remarks
2SC5200RTU	C5200R	TO-264	TUBE	hFE1 R grade
2SC5200OTU	C5200O	TO-264	TUBE	hFE1 O grade
FJL4315RTU	J4315R	TO-264	TUBE	hFE1 R grade
FJL4315OTU	J4315O	TO-264	TUBE	hFE1 O grade

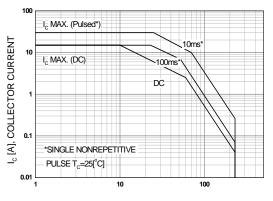


© 2009 Fairchild Semiconductor Corporation 2SC5200/FJL4315 Rev. C 2SC5200/FJL4315 — NPN Epitaxial Silicon Transistor

## **Typical Characteristics**







 $\mathsf{V}_{\mathsf{CE}}\left[\mathsf{V}\right]\!,$  COLLECTOR-EMITTER VOLTAGE

Figure 8. Safe Operating Area

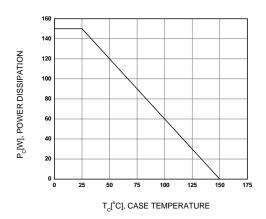
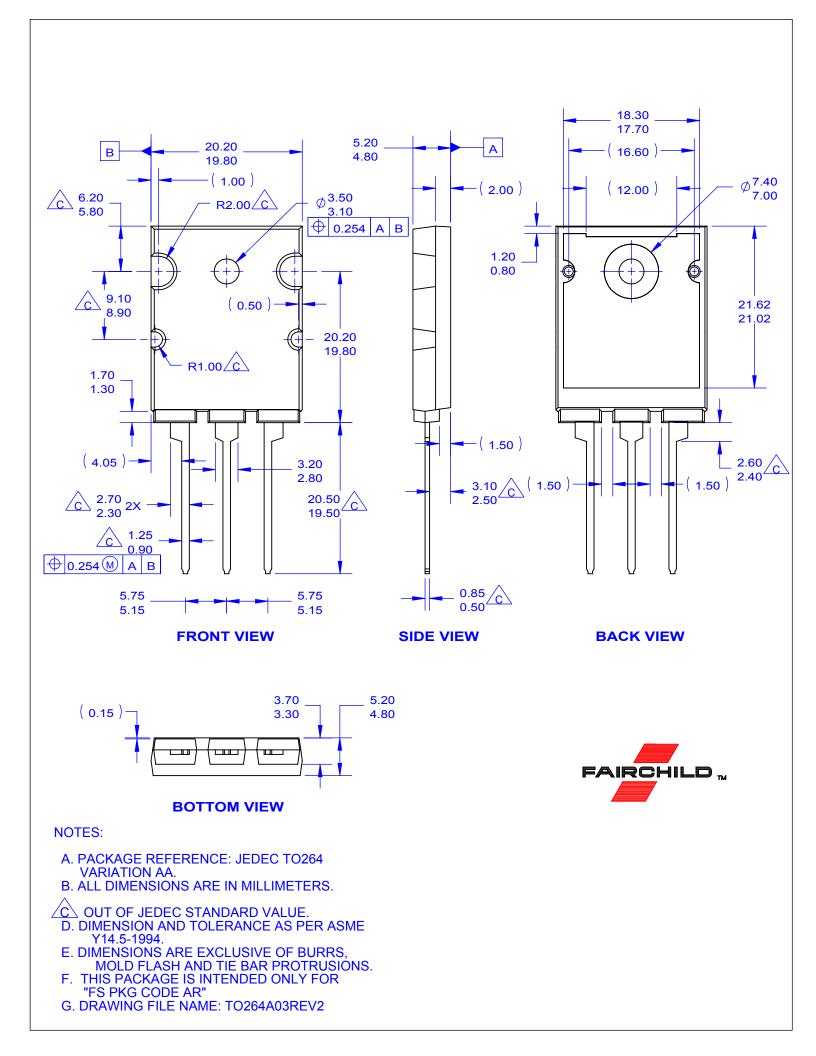


Figure 9. Power Derating

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